

# NVD5117PL

## Power MOSFET

**-60 V, 16 mΩ, -61 A, Single P-Channel**

### Features

- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- High Current Capability
- Avalanche Energy Specified
- AEC-Q101 Qualified
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

**MAXIMUM RATINGS** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	-60	V
Gate-to-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current $R_{\theta JC}$ (Note 1)	$I_D$	-61	A
		-43	
Power Dissipation $R_{\theta JC}$ (Note 1)	$P_D$	118	W
		59	
Continuous Drain Current $R_{\theta JA}$ (Notes 1 & 2)	$I_D$	-11	A
		-8	
Power Dissipation $R_{\theta JA}$ (Notes 1 & 2)	$P_D$	4.1	W
		2.1	
Pulsed Drain Current	$I_{DM}$	-419	A
Current Limited by Package (Note 3)	$I_{Dmaxpkg}$	60	A
Operating Junction and Storage Temperature	$T_J, T_{stg}$	-55 to 175	°C
Source Current (Body Diode)	$I_S$	-118	A
Single Pulse Drain-to-Source Avalanche Energy ( $T_J = 25^\circ\text{C}$ , $V_{DD} = 50$ V, $V_{GS} = 10$ V, $I_{L(pk)} = 40$ A, $L = 0.3$ mH, $R_G = 25$ Ω)	$E_{AS}$	240	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	$T_L$	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

### THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Drain)	$R_{\theta JC}$	1.3	°C/W
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	37	

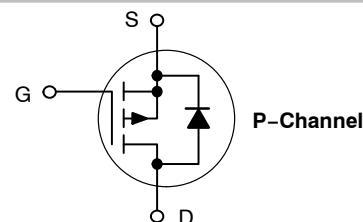
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



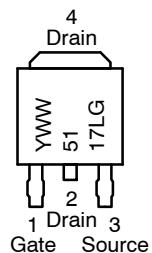
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$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D$
-60 V	16 mΩ @ -10 V	
	22 mΩ @ -4.5 V	-61 A



### MARKING DIAGRAMS & PIN ASSIGNMENT



Y = Year  
 WW = Work Week  
 5117L = Device Code  
 G = Pb-Free Package

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NVD5117PLT4G	DPAK (Pb-Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NVD5117PL

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>							
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA		-60			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = -60 V	T <sub>J</sub> = 25°C			-1.0	μA
			T <sub>J</sub> = 125°C			-100	
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V				±100	nA
<b>ON CHARACTERISTICS (Note 4)</b>							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = -250 μA		-1.5		-2.5	V
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -29 A			12	16	mΩ
		V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -29 A			16	22	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = -15 V, I <sub>D</sub> = -15 A			30		S
<b>CHARGES AND CAPACITANCES</b>							
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, f = 1.0 MHz, V <sub>DS</sub> = -25 V			4800		pF
Output Capacitance	C <sub>oss</sub>				480		
Reverse Transfer Capacitance	C <sub>rss</sub>				320		
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>DS</sub> = -48 V, I <sub>D</sub> = -29 A	V <sub>GS</sub> = -4.5 V		49		nC
			V <sub>GS</sub> = -10 V		85		
Threshold Gate Charge	Q <sub>G(TH)</sub>	V <sub>GS</sub> = -4.5 V, V <sub>DS</sub> = -48 V, I <sub>D</sub> = -29 A			3		
Gate-to-Source Charge	Q <sub>GS</sub>				13		
Gate-to-Drain Charge	Q <sub>GD</sub>				28		
Plateau Voltage	V <sub>GP</sub>				3.2		V
<b>SWITCHING CHARACTERISTICS (Notes 4)</b>							
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = -4.5 V, V <sub>DS</sub> = -48 V, I <sub>D</sub> = -29 A, R <sub>G</sub> = 2.5 Ω			22		ns
Rise Time	t <sub>r</sub>				195		
Turn-Off Delay Time	t <sub>d(off)</sub>				50		
Fall Time	t <sub>f</sub>				132		
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b>							
Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -29 A	T <sub>J</sub> = 25°C		-0.86	-1.0	V
			T <sub>J</sub> = 125°C		-0.74		
Reverse Recovery Time	t <sub>RR</sub>	V <sub>GS</sub> = 0 V, dI <sub>S</sub> /dt = 100 A/μs, I <sub>S</sub> = -29 A			36		ns
Charge Time	t <sub>a</sub>				19		
Discharge Time	t <sub>b</sub>				17		
Reverse Recovery Charge	Q <sub>RR</sub>				44		nC

4. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

## TYPICAL CHARACTERISTICS

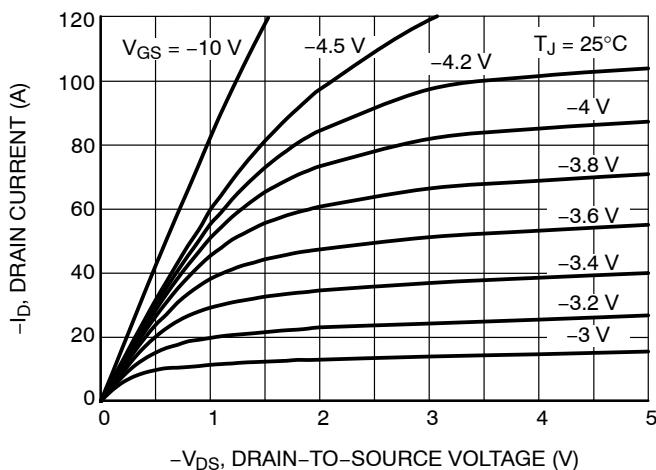


Figure 1. On-Region Characteristics

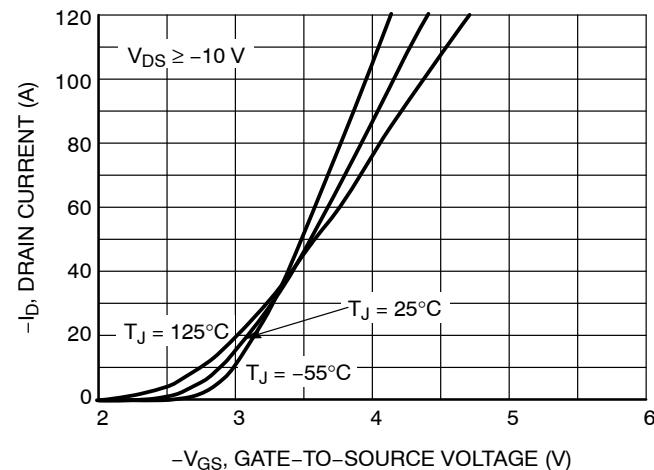


Figure 2. Transfer Characteristics

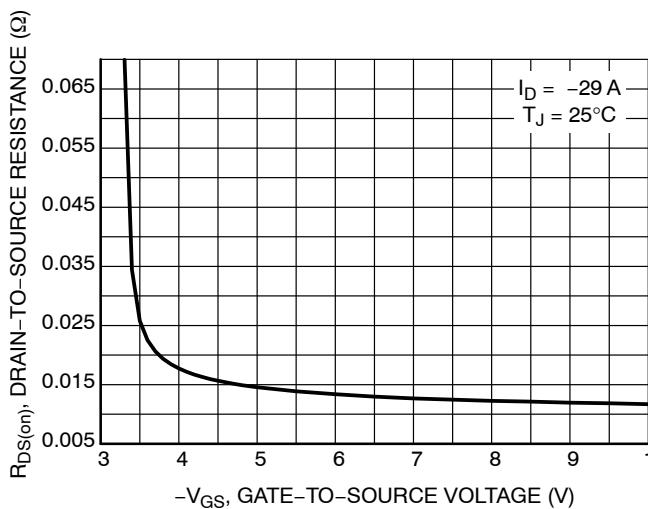


Figure 3. On-Resistance vs. Gate-to-Source Voltage

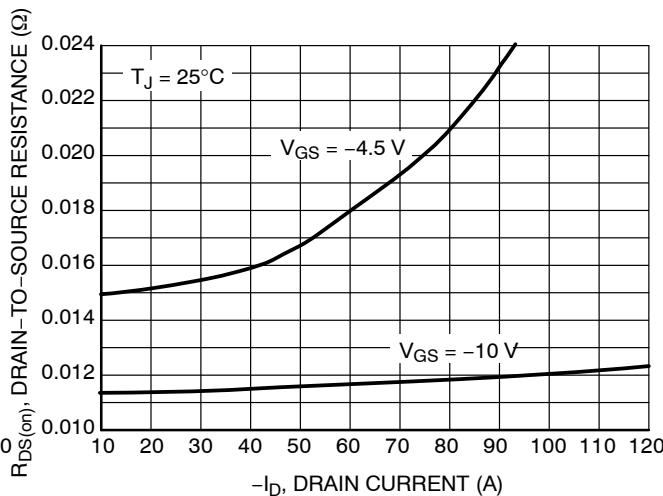


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

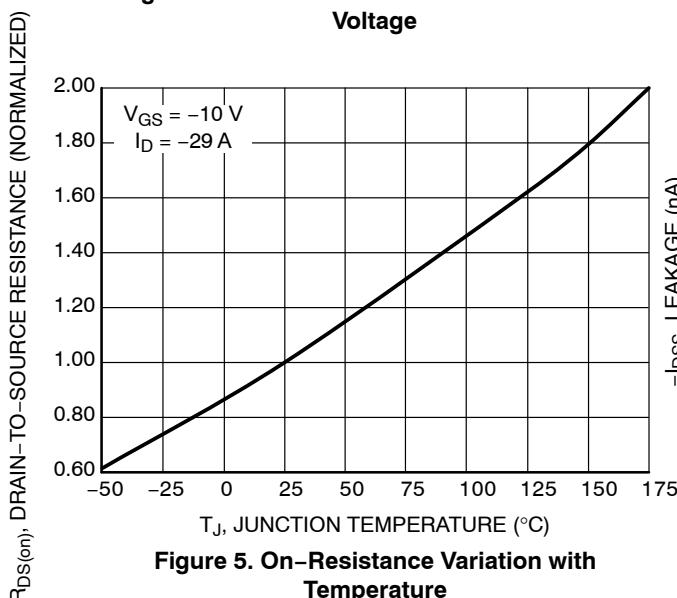


Figure 5. On-Resistance Variation with Temperature

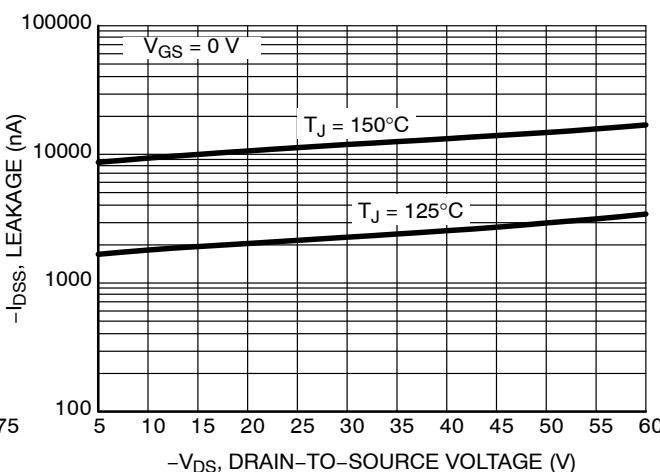
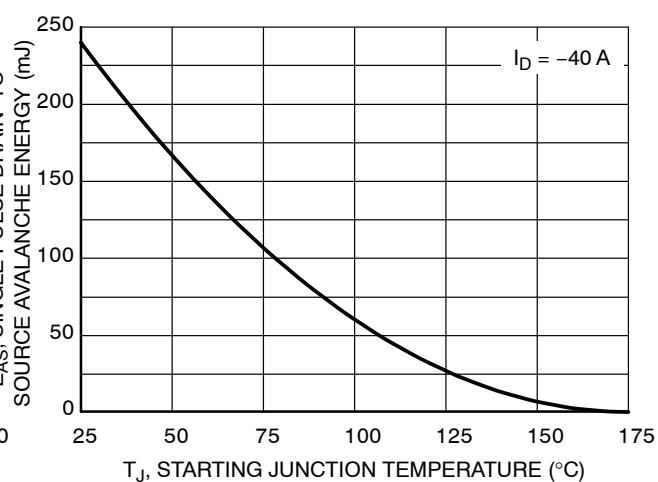
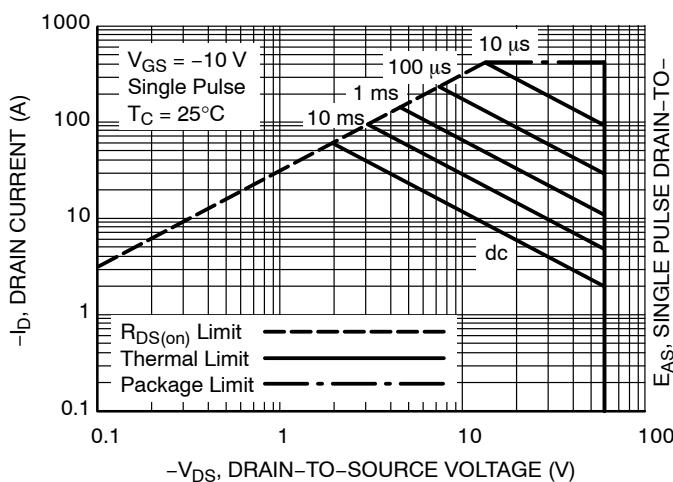
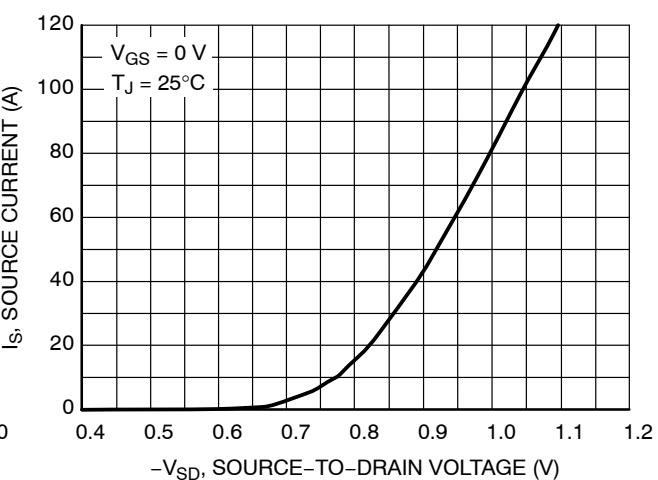
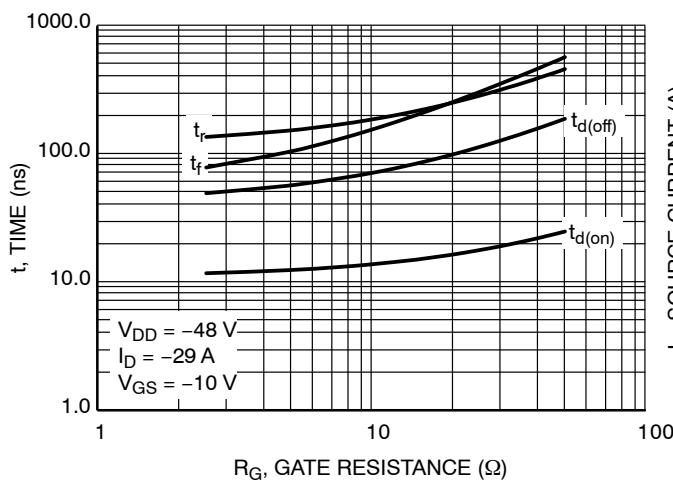
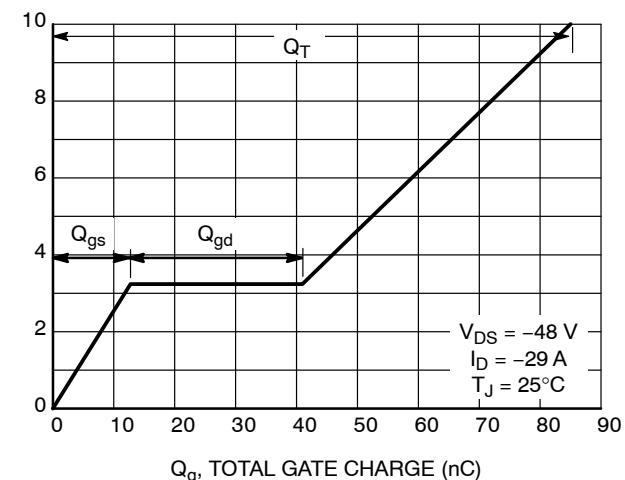
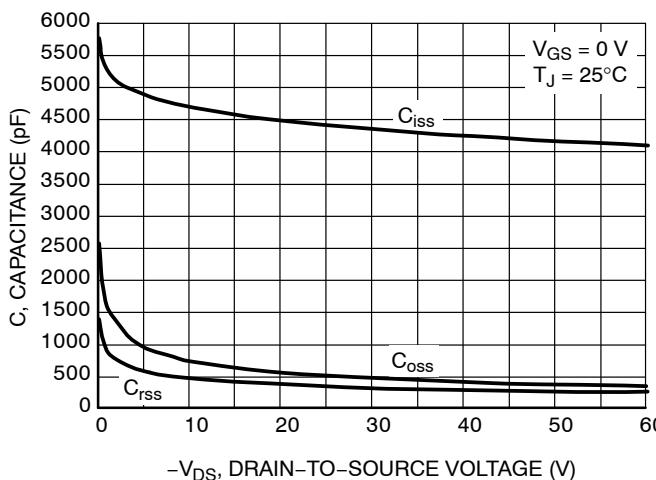


Figure 6. Drain-to-Source Leakage Current vs. Voltage

## TYPICAL CHARACTERISTICS



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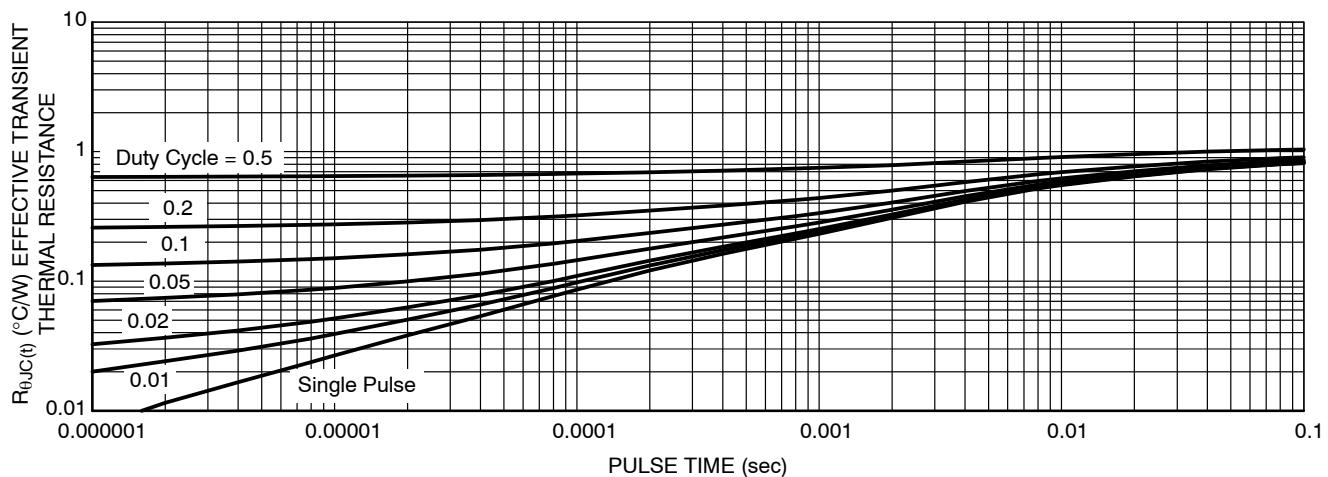
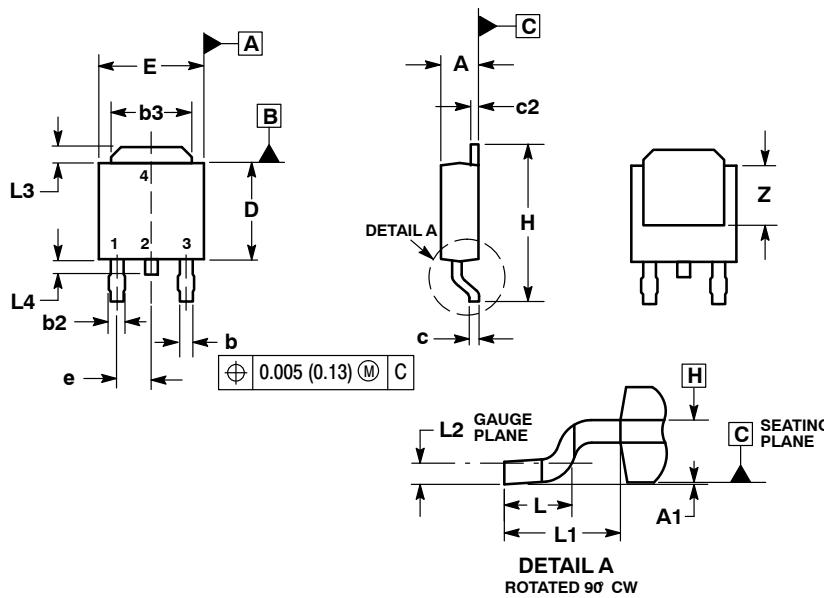


Figure 13. Thermal Response

## PACKAGE DIMENSIONS

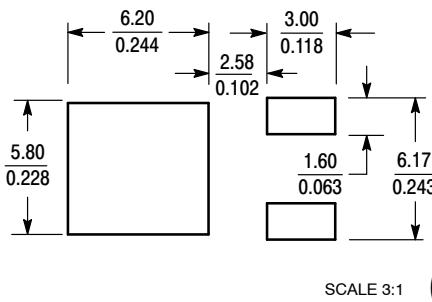
DPAK (SINGLE GAUGE)  
CASE 369C-01  
ISSUE D

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090	BSC	2.29	BSC
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108	REF	2.74	REF
L2	0.020	BSC	0.51	BSC
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

## SOLDERING FOOTPRINT\*



SCALE 3:1  $(\frac{\text{mm}}{\text{inches}})$

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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